

Sonic Fast Recovery Diode

1600 V 60 A

230 ns

High Performance Fast Recovery Diode Low Loss and Soft Recovery Parallel legs

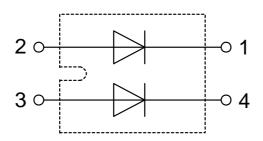
Part number

DH2x61-16A



Backside: Isolated





Features / Advantages:

- Planar passivated chips
- Very low leakage current
- · Very short recovery time
- Improved thermal behaviour
- Very low Irm-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low Irm reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- · Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: SOT-227B (minibloc)

- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Base plate: Copper internally DCB isolated
- Advanced power cycling

Terms Conditions of usage:

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office.

Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

to perform joint risk and quality assessments;
the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

IXYS reserves the right to change limits, conditions and dimensions.

Data according to IEC 60747 and per semiconductor unless otherwise specified

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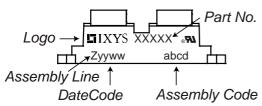


Fast Diode				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{RSM}	max. non-repetitive reverse blocking voltage		$T_{VJ} = 25^{\circ}C$			1600	V
V _{RRM}	max. repetitive reverse blocking ve	oltage	$T_{VJ} = 25^{\circ}C$			1600	V
I _R	reverse current, drain current	V _R =1600 V	$T_{VJ} = 25^{\circ}C$			200	μA
		$V_R = 1600 \text{ V}$	$T_{VJ} = 125$ °C			2	mΑ
V _F	forward voltage drop	I _F = 60 A	$T_{VJ} = 25^{\circ}C$			2.01	V
		$I_F = 120 A$				2.51	V
		$I_F = 60 \text{ A}$	T _{VJ} = 125°C			2.02	V
		$I_F = 120 \text{ A}$				2.71	V
I _{FAV}	average forward current	$T_c = 55^{\circ}C$	T _{vJ} = 150°C			60	Α
		rectangular d = 0.5					
V _{F0}	threshold voltage	$T_{VJ} = 150$ °C			1.28	V	
r _F	slope resistance for power lo	s calculation only				11.1	mΩ
R _{thJC}	thermal resistance junction to case	9				0.6	K/W
R _{thCH}	thermal resistance case to heatsin	k			0.10		K/W
P _{tot}	total power dissipation		$T_C = 25^{\circ}C$			200	W
I _{FSM}	max. forward surge current	$t = 10 \text{ ms}$; (50 Hz), sine; $V_R = 0 \text{ V}$	$T_{VJ} = 45^{\circ}C$			700	Α
C	junction capacitance	$V_R = 1200 V$ $f = 1 MHz$	$T_{VJ} = 25^{\circ}C$		32		pF
I _{RM}	max. reverse recovery current		$T_{VJ} = 25 ^{\circ}\text{C}$		60		Α
		$I_F = 60 \text{ A}; V_R = 1200 \text{ V}$	$T_{VJ} = 100^{\circ}C$		70		Α
t _{rr}	reverse recovery time	$\begin{cases} I_F = 60 \text{ A}; V_R = 1200 \text{ V} \\ -di_F /dt = 800 \text{ A/µs} \end{cases}$	$T_{VJ} = 25 ^{\circ}\text{C}$		230		ns
	,	1	$T_{VJ} = 100^{\circ}\text{C}$		350		ns



Package	Package SOT-227B (minibloc)			Ratings				
Symbol	Definition	Conditions			min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal					100	Α
T _{VJ}	virtual junction temperature				-40		150	°C
T _{op}	operation temperature				-40		125	°C
T_{stg}	storage temperature				-40		150	°C
Weight						30		g
M _D	mounting torque				1.1		1.5	Nm
$\mathbf{M}_{_{T}}$	terminal torque				1.1		1.5	Nm
d _{Spp/App}	oroonago distanco on surfe	oco I etrikina dietaneo through air	terminal to terminal 10.5 triking distance through air terminal to backside 8.6		3.2			mm
$d_{Spb/Apb}$	creepage distance on suna	ace striking distance through an			6.8			mm
V _{ISOL}	isolation voltage	t = 1 second	50/60 Hz, RMS; lisoL ≤ 1 mA		3000			V
.002		t = 1 minute			2500			V

Product Marking



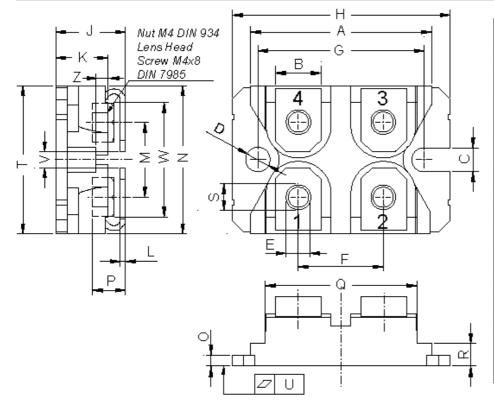
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DH2x61-16A	DH2x61-16A	Tube	10	511261

Similar Part	Package	Voltage class
DH2x60-18A	SOT-227B (minibloc)	1800
DH2x61-18A	SOT-227B (minibloc)	1800

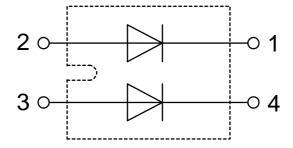
Equivalent Circuits for Simulation			* on die level	$T_{VJ} = 150 ^{\circ}\text{C}$
$I \rightarrow V_0$)— <u>R</u> o	Fast Diode		
V _{0 max}	threshold voltage	1.28		V
R _{0 max}	slope resistance *	9.3		mΩ



Outlines SOT-227B (minibloc)



Dim.	Millimeter		Inches		
Dim.	min	max	min	max	
Α	31.50	31.88	1.240	1.255	
В	7.80	8.20	0.307	0.323	
С	4.09	4.29	0.161	0.169	
D	4.09	4.29	0.161	0.169	
Е	4.09	4.29	0.161	0.169	
F	14.91	15.11	0.587	0.595	
G	30.12	30.30	1.186	1.193	
Н	37.80	38.23	1.488	1.505	
J	11.68	12.22	0.460	0.481	
K	8.92	9.60	0.351	0.378	
L	0.74	0.84	0.029	0.033	
M	12.50	13.10	0.492	0.516	
N	25.15	25.42	0.990	1.001	
0	1.95	2.13	0.077	0.084	
Р	4.95	6.20	0.195	0.244	
Q	26.54	26.90	1.045	1.059	
R	3.94	4.42	0.155	0.167	
S	4.55	4.85	0.179	0.191	
Т	24.59	25.25	0.968	0.994	
U	-0.05	0.10	-0.002	0.004	
V	3.20	5.50	0.126	0.217	
W	19.81	21.08	0.780	0.830	
Z	2.50	2.70	0.098	0.106	





Fast Diode

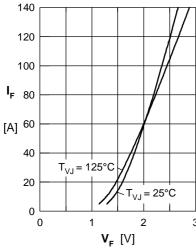


Fig. 1 Typ. rward current I_F versus V_F

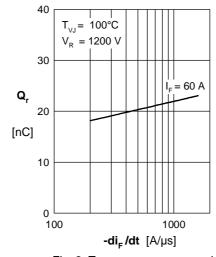


Fig. 2 Typ. reverse recovery charge Q_r versus $-di_F/dt$

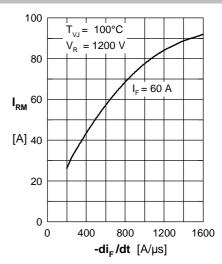


Fig. 3 Typ. peak reverse current $I_{\rm RM}$ versus $-{\rm di_F}/{\rm dt}$

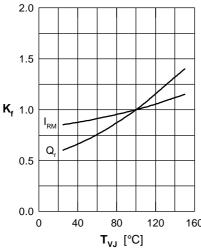
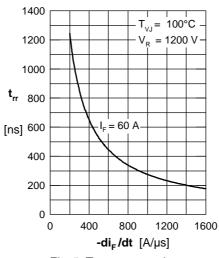


Fig. 4 Dynamic parameters $Q_{\rm r}$, $I_{\rm RM}$ versus $T_{\rm VJ}$



 $\begin{array}{ccc} \text{Fig. 5} & \text{Typ. recovery time} \\ & \text{t_{rr} versus $-di_{\text{F}}$/dt} \end{array}$

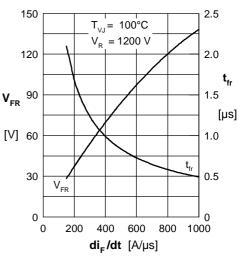


Fig. 6 Typ. peak forward voltage V_{FR} & typ. forward recovery time $t_{\rm fr}$ versus $di_{\rm F}/dt$

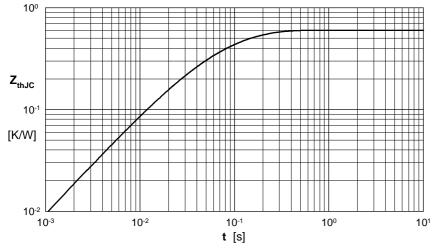


Fig. 7 Transient thermal resistance junction to case

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t _i (s)
1	0.212	0.0055
2	0.248	0.0092
3	0.063	0.0007
4	0.077	0.0391